

1.	Record Nr.	UNISOBSOBE00072191
	Autore	Vivaldi, Vincenzo
	Titolo	Due lavori su Giacomo Leopardi / Vincenzo Vivaldi
	Pubbl/distr/stampa	Catanzaro, : Tip. del giornale il Sud, 1898
	Titolo uniforme	Due lavori su Giacomo Leopardi
	Descrizione fisica	105 p. ; 21 cm
	Lingua di pubblicazione	Italiano
	Formato	Materiale a stampa
	Livello bibliografico	Monografia
2.	Record Nr.	UNINA9910438039203321
	Autore	Maricau Elie
	Titolo	Analog IC reliability in nanometer CMOS // Elie Maricau, Georges Gielen
	Pubbl/distr/stampa	New York, NY, : Springer Science, c2013
	ISBN	1-299-19739-6 1-4614-6163-4
	Edizione	[1st ed. 2013.]
	Descrizione fisica	1 online resource (xvi, 198 pages) : illustrations (some color)
	Collana	Analog circuits and signal processing
	Altri autori (Persone)	GielenGeorges
	Disciplina	621.3815
	Soggetti	Linear integrated circuits - Reliability Metal oxide semiconductors, Complementary
	Lingua di pubblicazione	Inglese
	Formato	Materiale a stampa
	Livello bibliografico	Monografia
	Note generali	Description based upon print version of record.
	Nota di bibliografia	Includes bibliographical references and index.
	Nota di contenuto	Introduction -- CMOS Reliability Overview -- Transistor Aging Compact Modeling -- Background on IC Reliability Simulation -- Analog IC Reliability Simulation -- Integrated Circuit Reliability -- Conclusions.
	Sommario/riassunto	This book focuses on modeling, simulation and analysis of analog circuit aging. First, all important nanometer CMOS physical effects resulting in circuit unreliability are reviewed. Then, transistor aging

compact models for circuit simulation are discussed and several methods for efficient circuit reliability simulation are explained and compared. Ultimately, the impact of transistor aging on analog circuits is studied. Aging-resilient and aging-immune circuits are identified and the impact of technology scaling is discussed. The models and simulation techniques described in the book are intended as an aid for device engineers, circuit designers and the EDA community to understand and to mitigate the impact of aging effects on nanometer CMOS ICs. · Enables readers to understand long-term reliability of an integrated circuit; · Reviews CMOS unreliability effects, with focus on those that will emerge in future CMOS nodes; · Provides overview of models for key aging effects, as well as compact models that can be included in a circuit simulator, with model parameters for advanced CMOS technology; · Describes existing reliability simulators, along with techniques to analyze the impact of process variations and aging on an arbitrary analog circuit.
